

# 深圳市晶泰源电子有限公司

BU102 TRANSISTOR(NPN)

## FEATURES

Power dissipation

PCM:0.8W(Tamb=25°C)

Collector current

ICM:0.35A

Collector-base voltage

V(BR)CBO: 600V

Operating and storage junction temperature range

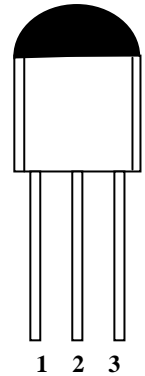
TJ,Tstg:-65°C to -150°C

T0-92

1.BASE

2.COLLECTOR

3. EMITTER



ELECTRICAL CHARACTERISTICS(Tamb=25°C unless otherwise specified):

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V(BR)CBO	IC=1mA, IE=0	600			V
Collector-emitter breakdown voltage	V(BR)CEO	IC=1mA, IB=0	400			V
Emitter-base breakdown voltage	V(BR)EBO	IC=1mA, IC=0	9			V
Collector cut-off current	ICBO	VCB=600V, IE=0			0.5	μA
Collector cut-off current	ICEO	Vce=400V, IB=0			1.0	μA
Emitter cut-off current	IEBO	VEB=9V, IC=0			0.1	μA
DC current gain	HFE	Vce=5V, IC=1mA	10		40	
Collector-emitter saturation voltage	VCE(sat)	IC=100mA, IB=20mA			0.6	V
Base-emitter saturation voltage	VBE(sat)	IC=100mA, IB=20mA			1.5	V
Storage time	ts	VCC=250V IC=5IB; IB1=IB2=60mA			5.5	us

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